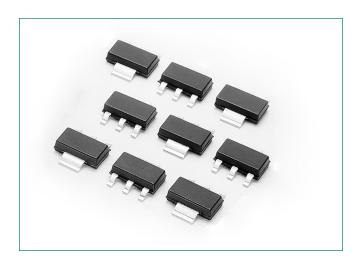


NYC222, NYC226, NYC228





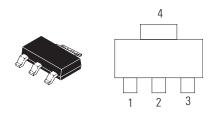
Description

Designed and tested for repetitive peak operation required for CD ignition, fuel ignitors, flash circuits, motor controls and low-power switching applications.

Features

- Blocking Voltage to 600 V
- High Surge Current 15 A
- Very Low Forward "On" Voltage at High Current
- Low-Cost Surface Mount SOT–223 Package
- These are Pb-Free Devices

Pin Out



Pin Assignment					
1	K (Cathode)				
2	A (Anode)				
3	Gate				
4	A (Anode)				

Functional Diagram





Maximum Ratings $(T_1 = 25^{\circ}C \text{ unless otherwise noted})$

Rating	Symbol	Value	Unit	
Peak Repetitive Off–State Voltage (Note 1) $(R_{GK} = I_K, T_J - 40 \text{ to } +110^{\circ}\text{C}, \text{ Sine Wave, } 50 \text{ to } 60 \text{ Hz})$	V _{DRM} ,	50 400 600	V	
On-State RMS Current (180° Conduction Angles; T _c = 80°C)		I _{T (RMS)}	1.5	А
Average On-State Current, (T _c = 65°C, f = 60 Hz, Time = 1 sec)		I _{T (AV)}	2.0	А
Peak Non-repetitive Surge Current, @T _A = 25°C, (1/2 Cycle, Sine Wave, 60 Hz)	I _{TSM}	15	А	
Circuit Fusing Considerations (t = 8.3 ms)	l²t	0.9	A ² s	
Forward Peak Gate Power (Pulse Width \leq 1.0 sec, $T_A = 25$ °C)	P _{GM}	0.5	W	
Forward Average Gate Power (t = 8.3 msec, T _A = 25°C)	P _{G (AV)}	0.1	W	
Forward Peak Gate Current (Pulse Width ≤ 1.0 s, T _A = 25°C)	I _{FGM}	0.2	А	
Reverse Peak Gate Voltage (Pulse Width $\leq 1.0 \mu s$, $T_A = 25^{\circ}C$)	V _{RGM}	5.0	V	
Operating Junction Temperature Range @ Rated V _{RRM} and V _{DRM}	T _J	-40 to +110	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient PCB Mounted	R _{eJA}	156	mW
Thermal Resistance, Junction—to—Tab Measured on MT2 Tab Adjacent to Epoxy	R _{eJT}	25	°C/W
Maximum Device Temperature for Soldering Purposes for 10 Secs Maximum	T _L	260	°C

Electrical Characteristics - **OFF** ($T_c = 25^{\circ}C$ unless otherwise noted)

Characteristic			Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T, = 25°C	I _{DRM} ,	-	-	10	μΑ
$(V_{AK} = V_{DRM} = V_{RRM}; RGK = 1000 \Omega)$	T _J = 110°C	IRRM	-	-	200	μΑ

Electrical Characteristics - ON (T₁ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Forward On-State Voltage (Note 2) (I _{TM} = 2.2 A Peak)			-	1.2	1.7	V
Gate Trigger Current (Note 3)	$T_{\rm C} = 25^{\circ}{\rm C}$		_	30	200	
$(V_{AK} = 7 \text{ V}, R_L = 100 \Omega)$	T _c =-40°C	GT	_	_	500	μΑ
Gate Trigger Voltage (dc) (Note 3)	$T_{\rm C} = 25^{\circ}{\rm C}$	\/	-	-	0.8	V
$(V_{AK} = 7 \text{ Vdc}, R_L = 100\Omega)$	T _c =-40°C	40°C	-	-	1.2	V
Gate Non-Trigger Voltage $(V_{AK} = V_{DRM'} R_L = 100 \Omega)$	T _C = 110°C	V _{GD}	0.1	-	-	V
Holding Current	T _C = 25°C		_	2.0	5.0	mA
$(V_{AK} = 12 \text{ V}, R_{GK} = 1000 \Omega)$ Initiating Current = 200 mA	T _c =-40°C	'н	_	_	10	IIIA

^{1.} V_{DRM} and V_{BRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



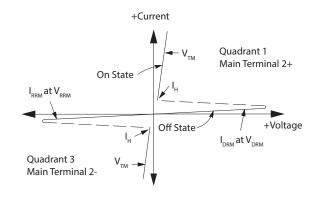
Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate-of-Rise of Off State Voltage (T _c = 110°C)	dv/dt	-	25	_	V/µs
Critical Rate of Rise of On–State Current ($T_{c} = 110^{\circ}\text{C}$, $I_{g} = 2 \times I_{gT}$, $R_{gK} = 1 \text{ k}\Omega$)	di/dt	-	20	_	A/µs

^{2.} Pulse Width = 1.0 ms, Duty Cycle $\leq 1\%$.

Voltage Current Characteristic of SCR

Symbol	Parameter			
V_{DRM}	Peak Repetitive Forward Off State Voltage			
I _{DRM}	I _{DRM} Peak Forward Blocking Current			
V _{RRM}	Peak Repetitive Reverse Off State Voltage			
I _{RRM}	Peak Reverse Blocking Current			
V _{TM} Maximum On State Voltage				
I _H	Holding Current			



^{3.} RGK Current not included in measurement.



Current Derating

Figure 1. Maximum Case Temperature

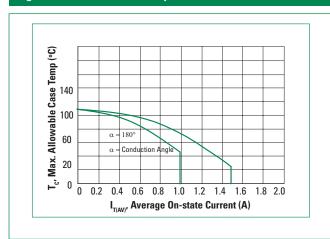


Figure 2. Maximum Ambient Temperature

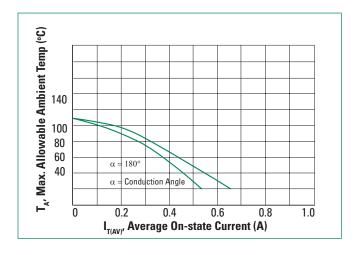


Figure 3. Typical Forward Voltage

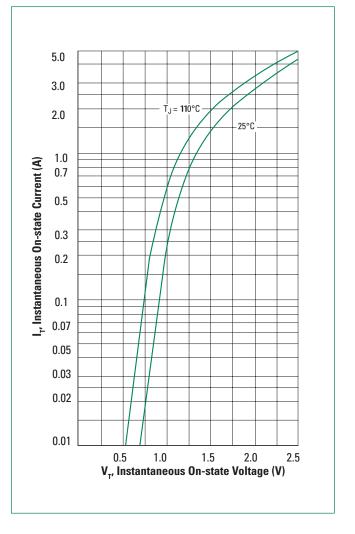


Figure 4. Thermal Response

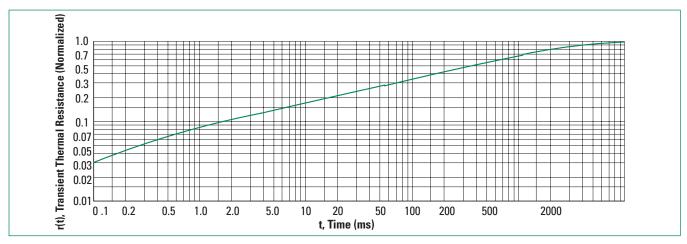




Figure 5. Typical Gate Trigger Voltage

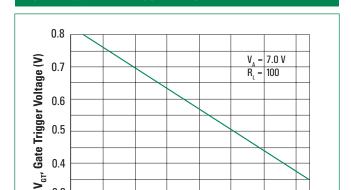


Figure 6. Typical Gate Trigger Current

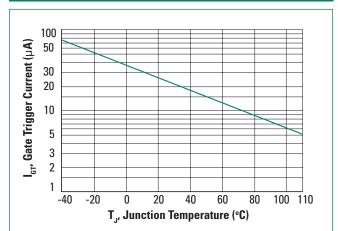


Figure 7. Typical Holding Current

-75 -50

-25

0

25

T_{.,'} Junction Temperature (°C)

50

75

100 110

0.4

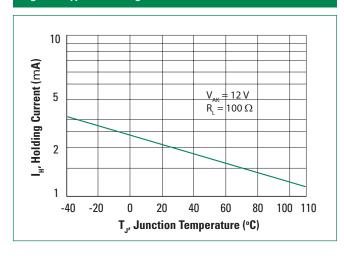
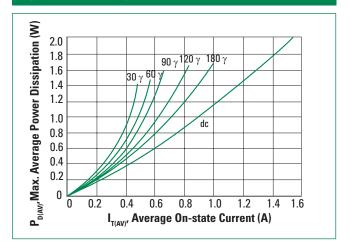
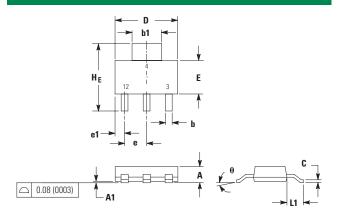


Figure 8. Power Dissipation





Dimensions



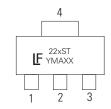
Dim	Dim		Inches		Millimeters		
Dilli	Min	Nom	Max	Min	Nom	Max	
Α			0.071			1.80	
A1	0.001	0.003	0.005	0.02	0.07	0.13	
b	0.026	0.030	0.033	0.66	0.75	0.84	
b1	0.114	0.118	0.122	2.90	3.00	3.10	
С	0.009	0.011	0.014	0.23	0.29	0.35	
D	0.260	0.260	0.264	6.60	6.60	6.71	
E	0.130	0.138	0.146	3.30	3.50	3.70	
е		0.091			2.30		
e1	0.030	0.037	0.045	0.75	0.95	1.15	
L1	0.059	0.069	0.079	1.50	1.75	2.00	
H _E	0.264	0.276	0.287	6.70	7.00	7.30	
ø	0°		10°	0°		10°	

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

Part Marking System



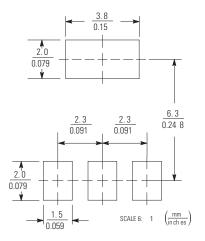
SOT-223 Case 318E Style 11



22xST = Device Code x =2, 6, or 8 Y = Year M = Month

A =Assembly Site XX =Lot Serial Code

Soldering Footprint



Ordering Information

Device	Package	Shipping
NYC222STT1G	SOT-223 (Pb-Free)	
NYC226STT1G	SOT-223 (Pb-Free)	1000/Tape & Reel
NYC228STT1G	SOT-223 (Pb-Free)	

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